Erratum to: A highly sensitive chemical gas detecting transistor based on highly crystalline CVD-grown MoSe₂ films

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The first affiliation of the authors in the original version of this article was unfortunately wrongly written on page 1861 and the first page of the ESM, instead of Multi-Functional Nano/Bio Electronics Lab., Kyung Hee University, Gyeonggi 446-701, Republic of Korea.

It should read

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